



STEVAL-TDR005V1

RF power amplifier using 2 x SD2943
N-channel enhancement-mode lateral MOSFETs

Features

- Excellent thermal stability
- Frequency: 1.8 - 54 MHz
- Supply voltage: 48 V
- Output power: 450 W typ.
- Input power 10 W max.
- Efficiency: 55 % - 76 %
- IMD at 300 WPEP < -24 dBc
- Load mismatch: 3:1 all phases

Description

The STEVAL-TDR005V1 is a RF broadband power amplifier intended for linear or nonlinear operation over the band 1.8 to 54 MHz using 2x SD2943 gold metallized N-channel MOS field-effect transistors. The temperature compensating biasing circuit supports class B and class AB operation.

STEVAL-TDR005V1 is designed in cooperation with Specific RF Devices (Germany).

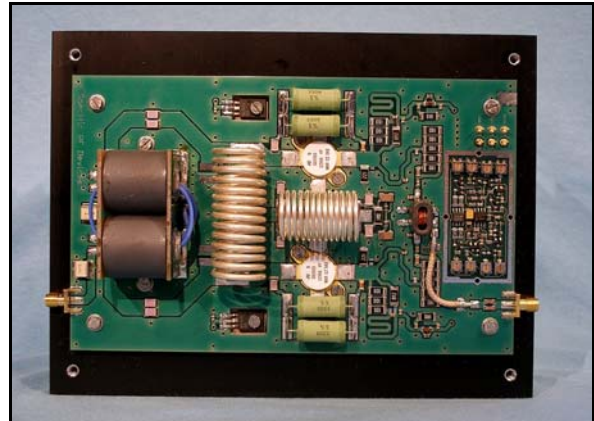


Table 1. Device summary

Order code
STEVAL-TDR005V1

Contents

1	Electrical data	3
	1.1 Maximum ratings	3
2	Electrical characteristics	4
3	Typical performance	5
4	Photos of STEVAL-TDR005V1 amplifier	6
5	STEVAL-TDR005V1 class of operation	7
6	SD2943 mounting recommendations	8
	6.1 Mounting recommendations	8
	6.2 Mounting sequence	8
7	Revision history	10

1 Electrical data

1.1 Maximum ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
P_{IN}	Input power	16	W
P_{OUT}	Output power	500	W
$V_{DD}^{(1)}$	Drain supply voltage	50	V
V_{GG}	Gate biasing voltage	15	V
I_{DD}	Drain current	20	A
P_{DISS}	Power dissipation	400	W

1. V_{GG} from 9 to 15 V and $P_{IN} < 16$ W

2 Electrical characteristics

$$T_A = +25\text{ }^\circ\text{C}, V_{DD} = 48\text{ V}, I_{DQ} = 2 \times 900\text{ mA}$$

Table 3. Electrical specification

Symbol	Test Conditions	Min	Typ	Max	Unit
Freq.	Frequency range	1.8		54	MHz
P _{OUT}	P _{IN} = 10 W	350	450		W
Gain	P _{IN} = 10 W	16.6 ± 0.6 dB			dB
ND	P _{IN} = 10 W	55 - 76			%
H2	2 ND Harmonic @ P _{OUT} = 300 W	-24 / -49			dBc
H3	3 RD Harmonic @ P _{OUT} = 300 W	-15 / -58			dBc
VSWR	Load mismatch all phases @ P _{OUT} = 300 W			3:1	

3 Typical performance

Figure 1. Output power vs frequency

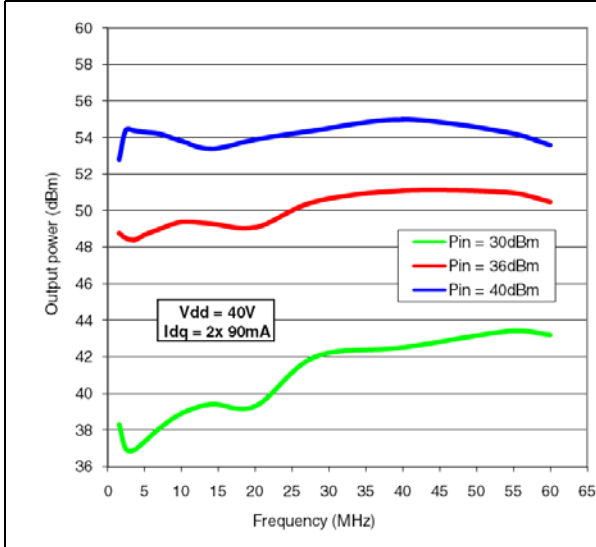
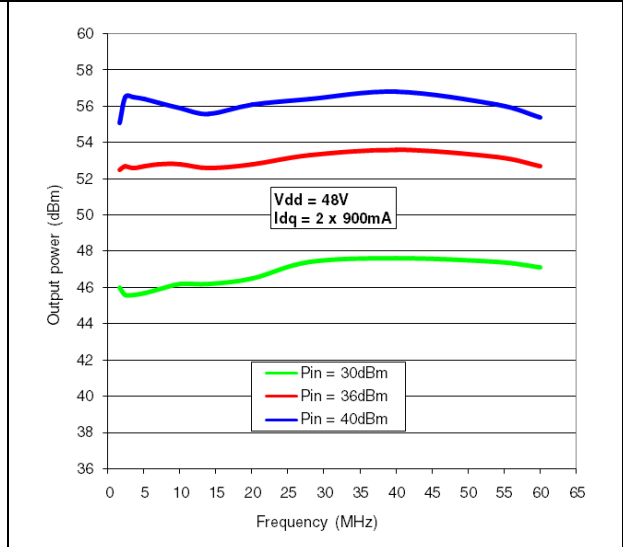


Figure 2. Output power vs frequency



4 Photos of STEVAL-TDR005V1 amplifier

Figure 3. Top view

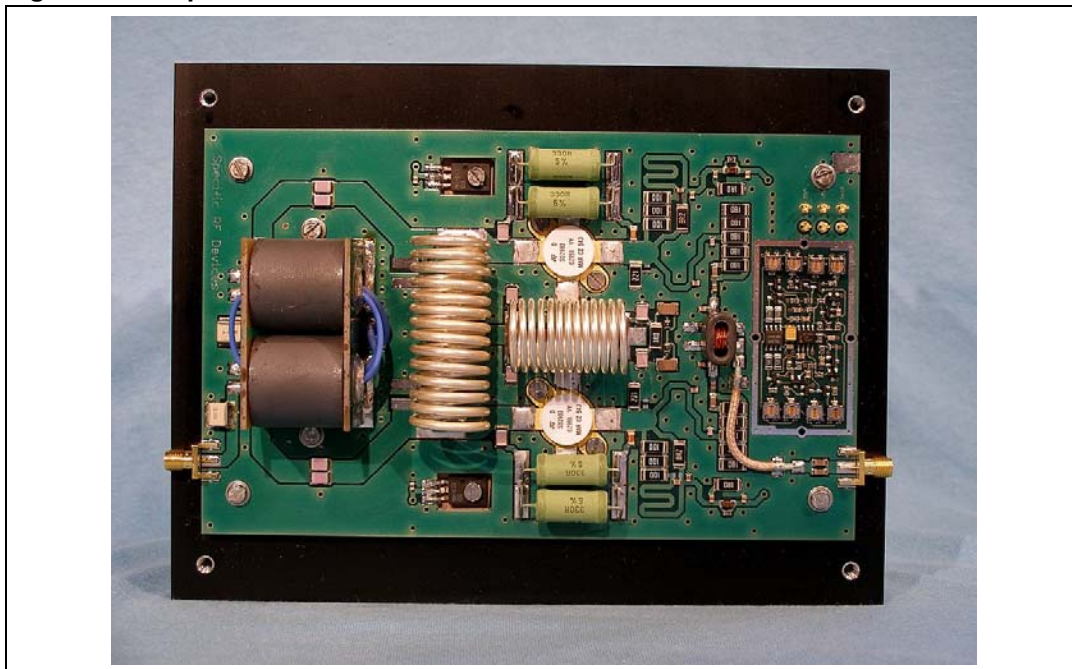
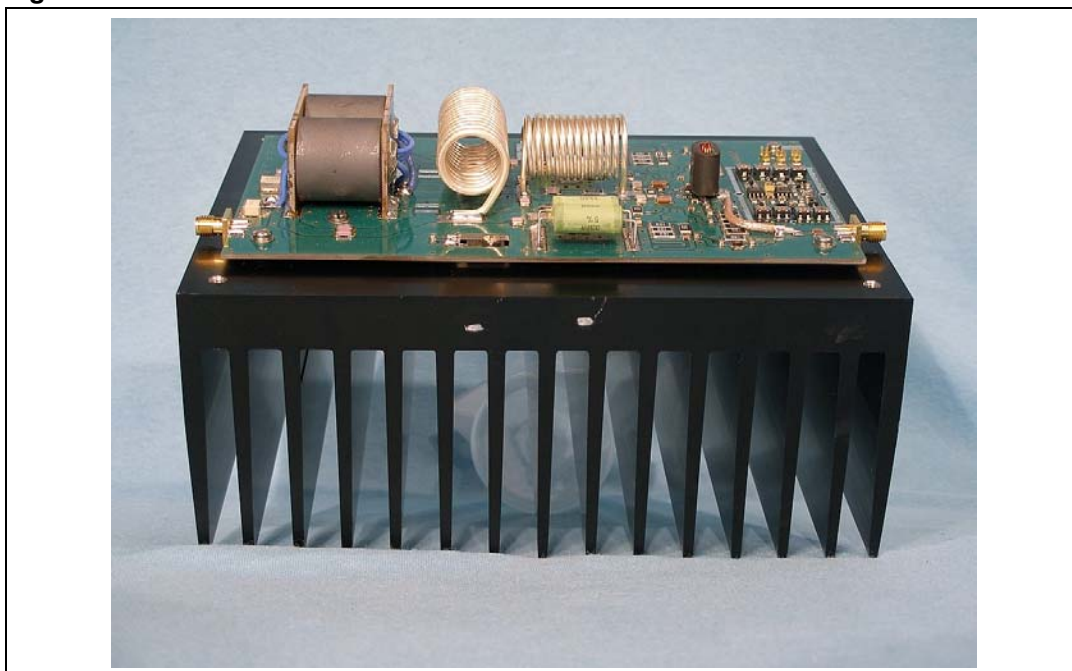


Figure 4. Side view



5 STEVAL-TDR005V1 class of operation

- Class B: a low bias point with ~100 mA per transistor
- Class AB: a higher bias point with ~ 900 mA per transistor

To select a bias point, STEVAL-TDR005V1 has a control port "BIAS".

- The bias point is 2x 100 mA if "BIAS" is left open and in this case a DC voltage of ~5 V is present
- The bias point is 2 x 900 mA if "BIAS" is connected to ground.

"PA_ON" control port / ON-OFF bias current

- To switch-on biasing circuit, connect "PA_ON" to ground.
- To switch-off biasing circuit, left open "PA_ON"

6 SD2943 mounting recommendations

6.1 Mounting recommendations

- Ensure holes in heatsinks are free from burrs;
- Minimum depth of tapped holes in heatsinks is 6 mm;
- Use 4-40 UNC-2A cheese-head screws with a flat washer to spread the joint pressure;
- The minimum flatness of the mounting area is 0.02 mm;
- Mounting area roughness should be less than 0.5 μm (micro);
- Avoid, as much as possible, use of flux or flux solutions because flux can penetrate even when hermetically sealed ceramic-capped transistors. Tin and wash the printed-circuit board BEFORE mounting the power transistors, then solder the transistor leads without using flux;
- Transistor leads may be tinned by dipping them full-length into a solder bath at a temperature of about 230 °C. No flux should be used during tinning;
- Recommended heatsink compounds: WPSII (silicon free) from austerlitz electronics, 340 from down corning etc.

6.2 Mounting sequence

- Apply a thin layer of evenly distributed heatsink compound to the flange;
- Position the device with flat washers in place;
- Tighten the screws until finger tight (0.05 Nm);
- Further tighten the screws until the specified torque is reached;
- For M174, M177 and M244 type of packages, torque should be minimum 0.6 Nm and 0.75 Nm max.

Table 4. DMOS packages - list of materials

Package Type	Description	Flange	Leadframe	Ceramic insulator	Plating		Torque (Nm)	
					Leads	Flange	Min	Max
M174	0.500 DIA 4L NON HERM W/FLANGE	Cu	ALLOY 42 (Fe58 / Ni42)	BeO (99.5% min)	Au (100µ min) over Ni (100µ min / 350µ max)	Ni(100µ min) + Pd (10µ min)	0.6	0.75
M174 (Moly disk)	0.500 DIA 4L NON HERM W/FLANGE (MOLY DISK)	Cu-Mo- Cu	ALLOY 42 (Fe58 / Ni42)	BeO (99.5% min)	Au (100µ min) over Ni (100µ min / 350µ max)	Ni(100µ min) + Pd (10µ min)	0.6	0.75
M177	0.550 DIA 4L NON HERM W/FLANGE	Cu-Mo- Cu	ALLOY 42 (Fe58 / Ni42)	BeO (99.5% min)	Au (60µ min) over Ni (100µ min / 350µ max)	Au (100µ min) over Ni (100µ min / 350µ max)	0.6	0.75
M244	2x 0.400x0.425 WIDE 2L LAP N/H FLANGE	W (85%) - Cu (15%)	ALLOY 42 (Fe58 / Ni42)	BeO (99.5% min)	Au (60µ min) over Ni (100µ min / 350µ max)	Au (60µ min) over Ni (100µ min / 350µ max)	0.6	0.75

7 Revision history

Table 5. Document revision history

Date	Revision	Changes
01-Jul-2008	1	Initial release.
18-Mar-2010	2	Updated description on cover page.

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